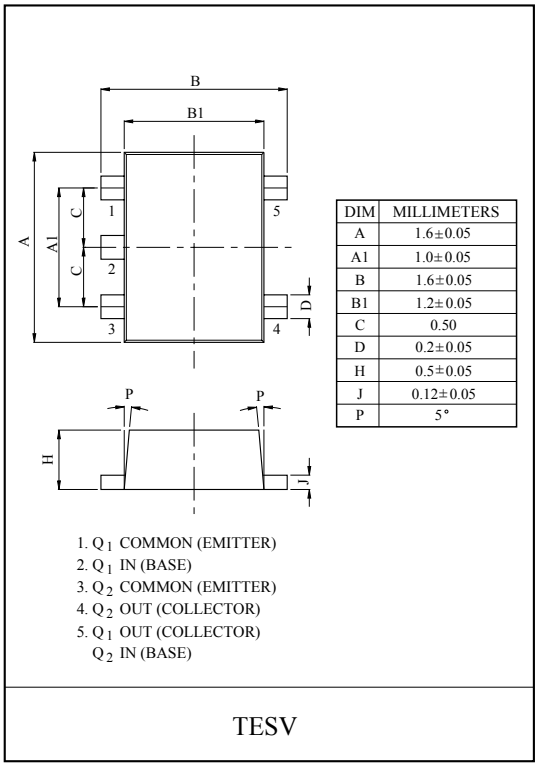
KRX102E

EPITAXIAL PLANAR NPN/PNP TRANSISTOR

SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

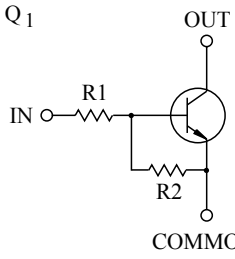
- Including two devices in TESV.
  (Thin Extreme Super mini type with 5 pin.)
- With Built-in bias resistors.
- Simplify circuit design.
- Reduce a quantity of parts and manufacturing process.

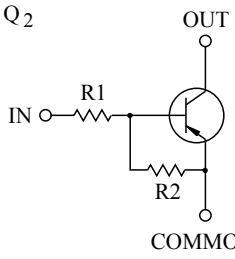


DIM	MILLIMETERS
A	1.6±0.05
A1	1.0±0.05
B	1.6±0.05
B1	1.2±0.05
C	0.50
D	0.2±0.05
H	0.5±0.05
J	0.12±0.05
P	5°

TESV

EQUIVALENT CIRCUIT

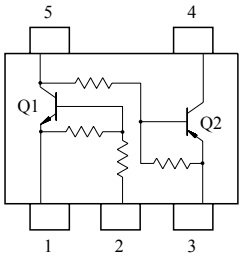




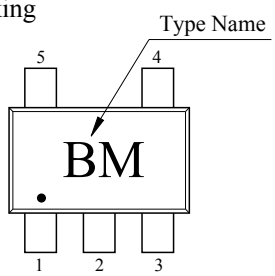
Q_1
R1=47KΩ
R2=47KΩ

Q_2
R1=10KΩ
R2=47KΩ

EQUIVALENT CIRCUIT (TOP VIEW)



Marking



Q1 MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Output Voltage	V_O	50	V
Input Voltage	V_I	40, -10	V
Output Current	I_O	100	㎃

Q2 MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Output Voltage	V_O	-50	V
Input Voltage	V_I	-30, 6	V
Output Current	I_O	-100	㎃

Q1, Q2 MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Power Dissipation	P_D *	200	㎽
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

* Total Raing.

Q1 ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT.
Output Cut-off Current	$I_{O(OFF)}$	V_O=50V, V_I=0	-	-	500	nA
DC Current Gain	G_I	V_O=5V, I_O=10mA	80	200	-	
Output Voltage	$V_{O(ON)}$	I_O=10mA, I_I=0.5mA	-	0.1	0.3	V
Input Voltage (ON)	$V_{I(ON)}$	V_O=0.2V, I_O=5mA	-	2.8	5.0	V
Input Voltage (OFF)	$V_{I(OFF)}$	V_O=5V, I_O=0.1mA	1.0	1.2	-	V
Transition Frequency	f_T *	V_O=10V, I_O=5mA	-	200	-	MHz
Input Current	I_I	V_I=5V	-	-	0.18	mA

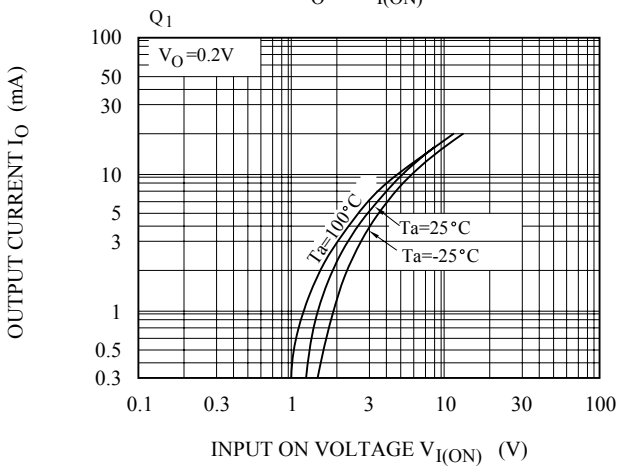
Note : * Characteristic of Transistor Only.

Q2 ELECTRICAL CHARACTERISTICS (Ta=25℃)

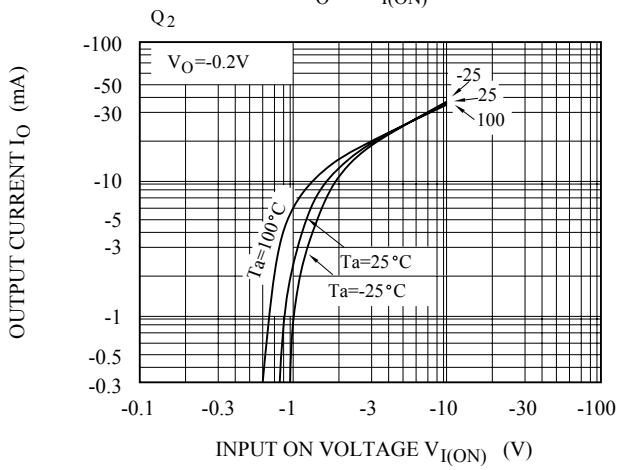
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT.
Output Cut-off Current	$I_{O(OFF)}$	V_O=-50V, V_I=0	-	-	-500	nA
DC Current Gain	G_I	V_O=-5V, I_O=-10mA	80	150	-	
Output Voltage	$V_{O(ON)}$	I_O=-10mA, I_I=-0.5mA	-	-0.1	-0.3	V
Input Voltage (ON)	$V_{I(ON)}$	V_O=-0.2V, I_O=-5mA	-	-1.2	-1.8	V
Input Voltage (OFF)	$V_{I(OFF)}$	V_O=-5V, I_O=-0.1mA	-0.5	-0.75	-	V
Transition Frequency	f_T *	V_O=-10V, I_O=-5mA	-	200	-	MHz
Input Current	I_I	V_I=-5V	-	-	-0.88	mA

Note : * Characteristic of Transistor Only.

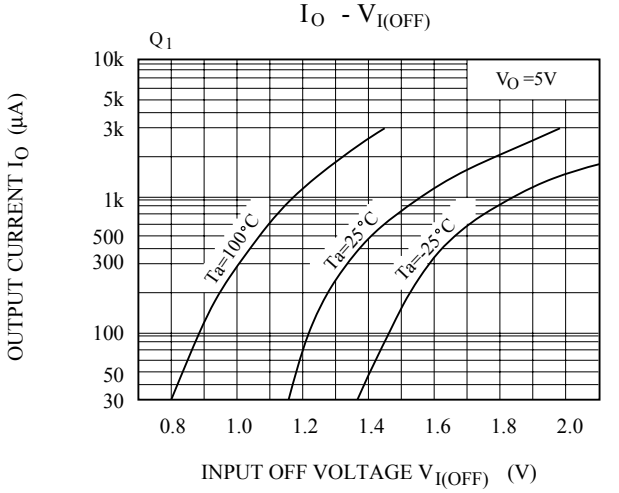
I_O - $V_{I(ON)}$



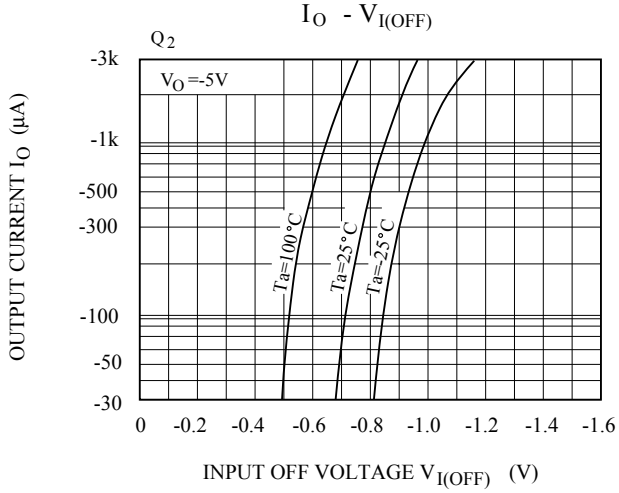
I_O - $V_{I(ON)}$



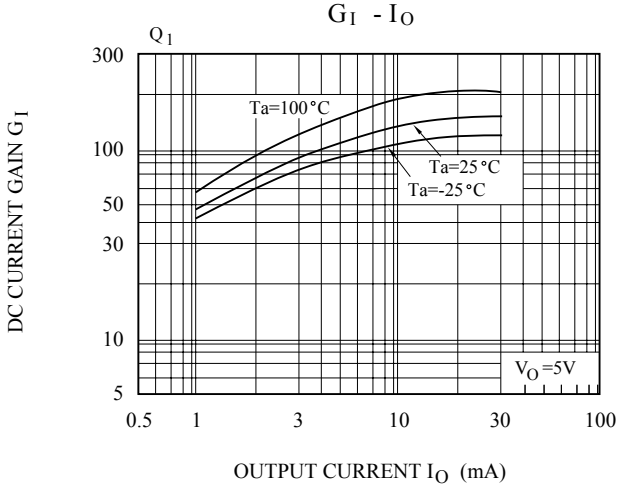
I_O - $V_{I(OFF)}$



I_O - $V_{I(OFF)}$



G_I - I_O



G_I - I_O

